MBR2535CTLG

Switch-mode Power Rectifier

Features and Benefits

- Low Forward Voltage
- Low Power Loss/High Efficiency
- High Surge Capacity
- 150°C Operating Junction Temperature
- 25 A Total (12.5 A Per Diode Leg)
- This Device is Pb-Free and is RoHS Compliant*

Applications

- Power Supply Output Rectification
- Power Management
- Instrumentation

Mechanical Characteristics

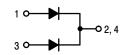
- Case: Epoxy, Molded
- Epoxy Meets UL 94, V-0 @ 0.125 in
- Weight: 1.9 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperatures for Soldering Purposes: 260°C Max. for 10 Seconds
- ESD Rating: Human Body Model 3B Machine Model C

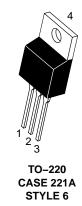


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SCHOTTKY BARRIER RECTIFIER 25 AMPERES, 35 VOLTS





MARKING DIAGRAM



А	= Assembly Location
Υ	= Year
WW	= Work Week
B2535	L = Device Code
G	= Pb-Free Package
AKA	= Polarity Designator

ORDERING INFORMATION

[Device	Package	Shipping
	MBR2535CTLG	TO-220 (Pb-Free)	50 Units/Rail

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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MAXIMUM RATINGS (Per Leg)

Rating	Symbol	Value	Unit V	
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	35		
Average Rectified Forward Current $(T_C = 142^{\circ}C \text{ per Diode})$ $(T_C = 142^{\circ}C \text{ per Device})$	I _{F(AV)}	12.5 25	A	
Peak Repetitive Forward Current, per Leg (Sq Wave, 20 kHz, $T_C = 139^{\circ}C$)	I _{FRM}	25	А	
Non–Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions, Halfwave, Single Phase, 60 Hz)	IFSM	150	A	
Peak Repetitive Reverse Surge Current (2.0 µs, 1.0 kHz)	I _{RRM}	1.0	А	
Storage Temperature Range	T _{stg}	-65 to +150	°C	
Operating Junction Temperature (Note 1)	TJ	-65 to +150	°C	
Voltage Rate of Change (Rated V _R)	dv/dt	10,000	V/µs	
Controlled Avalanche Energy	W _{aval}	20	mJ	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The heat generated must be less than the thermal conductivity from Junction-to-Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

THERMAL CHARACTERISTICS

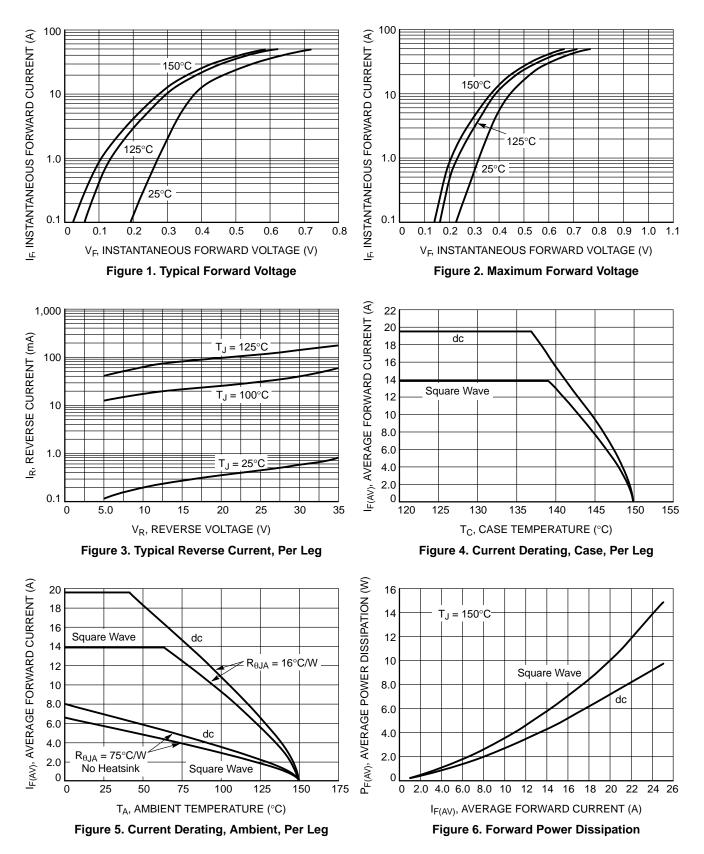
Characteristic	Conditions	Symbol	Max	Unit	
Maximum Thermal Resistance, Junction-to-Case	Min. Pad	$R_{ extsf{ heta}JC}$	2.0	°C/W	
Maximum Thermal Resistance, Junction-to-Ambient	Min. Pad	R_{\thetaJA}	75.0		

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min	Typical	Max	Unit
Instantaneous Forward Voltage (Note 2) ($i_F = 25 \text{ Amps}, T_j = 25^{\circ}C$) ($i_F = 12.5 \text{ Amps}, T_j = 25^{\circ}C$) ($i_F = 12.5 \text{ Amps}, T_j = 125^{\circ}C$)	۷F	- - -	0.51 0.41 0.33	0.55 0.47 0.41	V
Instantaneous Reverse Current (Note 2) (Rated dc Voltage, Tj = 25°C) (Rated dc Voltage, Tj = 125°C)	İR	-	0.8 300	5.0 500	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 2. Pulse Test: Pulse Width = $300 \ \mu$ s, Duty Cycle $\leq 2.0\%$.

MBR2535CTLG



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		TO-220 CASE 221A ISSUE AK						DATE	13 JAN 2022
SCALE 1:1			1. C 2. C 3. C	CONTR DIMEN LEAD	ROLLING DI ISION Z DEI D IRREGULA	MENSION FINES A ZO ARITIES AR	ONE WHERE AL E ALLOWED.		
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				в	0.380	0.415	9.66	10.53	
н —	₩₩			с	0.160	0.190	4.07	4.83	
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z_				F	0.142	0.161	3.60	4.09	
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V — + I I-	►- ``.			L	0.045	0.060	1.15	1.52	
G 	. <mark> </mark> ^{J−}			N	0.190	0.210	4.83	5.33	
· · · ·	- → D			Q	0.100	0.120	2.54	3.04	
	N 🖛			R	0.080	0.110	2.04	2.79	
				s	0.045	0.055	1.15	1.41	
				т	0.235	0.255	5.97	6.47	
				U	0.000	0.050	0.00	1.27	
				V	0.045		1.15		
				Z		0.080		2.04	
2. 3. 4. STYLE 5: PIN 1. 2.	BASE PIN 1. COLLECTOR 2. EMITTER 3. COLLECTOR 4. STYLE 6: GATE DRAIN 2.	EMITTER COLLECTOR EMITTER ANODE CATHODE	IN 1. CAT 2. ANO 3. GAT 4. ANO LE 7: IN 1. CAT 2. ANO	ode Te ode Thode ode		2. 3. 4. STYLE 8: PIN 1. 2.	MAIN TERMINAL MAIN TERMINAL GATE MAIN TERMINAL CATHODE ANODE	2	
4. STYLE 9: PIN 1.	DRAIN 4. STYLE 10 GATE PIN 1.	ANODE CATHODE GATE P SOURCE	3. CAT 4. ANO LE 11: IN 1. DR/ 2. SOU	ode Ain		4. STYLE 12: PIN 1.	EXTERNAL TRIP ANODE MAIN TERMINAL MAIN TERMINAL	. 1	
3.	EMITTER 3.	DRAIN SOURCE	3. GAT 4. SOL	ΤE		3.	GATE NOT CONNECTI		

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